

Preliminary

TOSHIBA Insulated Gate Bipolar Transistor Silicon N Channel IGBT

GT25Q102

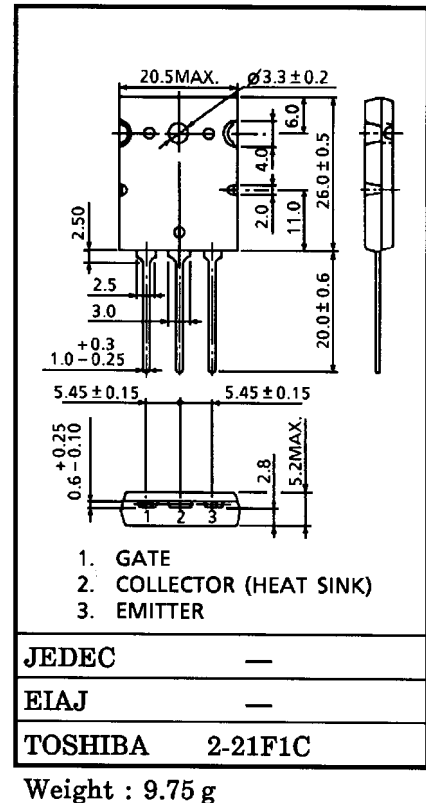
High Power Switching Applications

Unit in mm

- The 3rd Generation
- Enhancement-Mode
- High Speed: $t_f = 0.32 \mu s$ (max)
- Low Saturation Voltage: $V_{CE(sat)} = 2.7 V$ (max)

Maximum Ratings (Ta = 25°C)

Characteristic	Symbol	Rating	Unit
Collector-emitter voltage	V_{CES}	1200	V
Gate-emitter voltage	V_{GES}	± 20	V
Collector current	DC	I_C	25
	1 ms	I_{CP}	50
Collector power dissipation (Tc = 25°C)	P_C	200	W
Junction temperature	T_j	150	°C
Storage temperature range	T_{stg}	-55-150	°C



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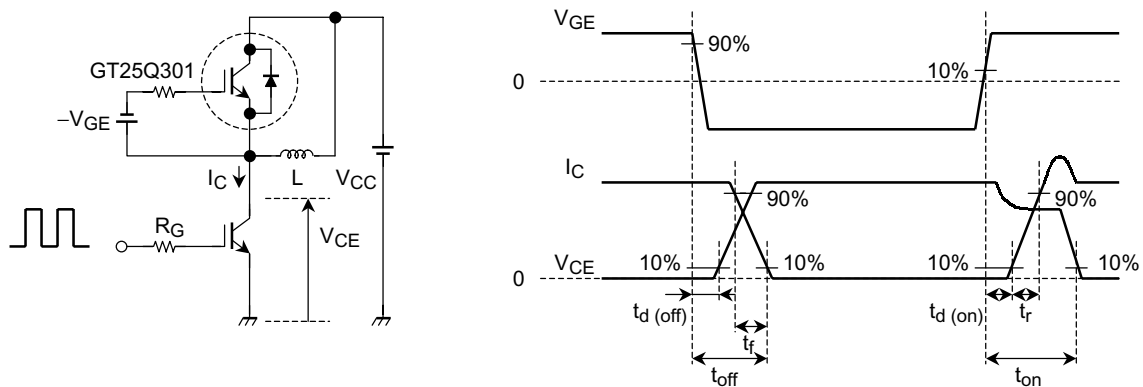
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Electrical Characteristics (Ta = 25°C)

Characteristic		Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current		I_{GES}	$V_{GE} = \pm 20\text{ V}, V_{CE} = 0$	—	—	± 500	nA
Collector cut-off current		I_{CES}	$V_{CE} = 1200\text{ V}, V_{GE} = 0$	—	—	1.0	mA
Gate-emitter cut-off voltage		$V_{GE (OFF)}$	$I_C = 2.5\text{ mA}, V_{CE} = 5\text{ V}$	4.0	—	7.0	V
Collector-emitter saturation voltage		$V_{CE (sat)}$	$I_C = 25\text{ A}, V_{GE} = 15\text{ V}$	—	2.1	2.7	V
Input capacitance		C_{ies}	$V_{CE} = 50\text{ V}, V_{GE} = 0, f = 1\text{ MHz}$	—	1360	—	pF
Switching time	Rise time	t_r	Inductive Load $V_{CC} = 600\text{ V}, I_C = 25\text{ A}$ $V_{GG} = \pm 15\text{ V}, R_G = 43\ \Omega$ (Note1)	—	0.10	—	μs
	Turn-on time	t_{on}		—	0.30	—	
	Fall time	t_f		—	0.16	0.32	
	Turn-off time	t_{off}		—	0.68	—	
Thermal resistance		$R_{th (j-c)}$	—	—	—	0.625	°C/W

Note1: Switching time measurement circuit and input/output waveforms



Note2: Switching loss measurement waveforms

